

## **Dual Series Schottky Barrier Diode**

## BAS40-04LT1G, SBAS40-04LT1G

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

#### **Features**

- Extremely Fast Switching Speed
- Low Forward Voltage
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Reverse Voltage	$V_{R}$	40	V
Forward Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>F</sub>	225 1.8	mW mW/°C
Operating Junction and Storage Temperature Range	T <sub>J,</sub> T <sub>stg</sub>	-55 to +150	°C
Forward Continuous Current	I <sub>FM</sub>	120	mA
	I <sub>FSM</sub>	200 600	mA
Thermal Resistance (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JA}$	508 311	°C/W

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

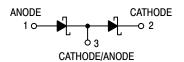
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- 1. FR-4 @ minimum pad.
- 2. FR-4 @ 1.0 x 1.0 in pad.

### 40 VOLTS SCHOTTKY BARRIER DIODES



SOT-23 (TO-236) CASE 318 STYLE 11



#### **MARKING DIAGRAM**



CB = Specific Device Code

M = Date Code\*= Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BAS40-04LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SBAS40-04LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

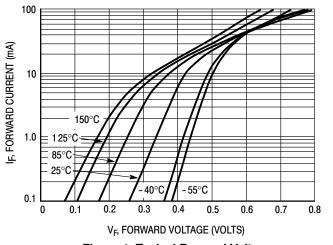
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### **BAS40-04LT1G, SBAS40-04LT1G**

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
Reverse Breakdown Voltage ( $I_R = 10 \mu A$ )	V <sub>(BR)R</sub>	40	-	V
Total Capacitance (V <sub>R</sub> = 1.0 V, f = 1.0 MHz)	C <sub>T</sub>	-	5.0	pF
Reverse Leakage (V <sub>R</sub> = 25 V)	I <sub>R</sub>	-	1.0	μΑ
Forward Voltage (I <sub>F</sub> = 1.0 mA)	V <sub>F</sub>	_	380	mV
Forward Voltage (I <sub>F</sub> = 10 mA)	V <sub>F</sub>	-	500	mV
Forward Voltage (I <sub>F</sub> = 40 mA)	V <sub>F</sub>	-	1.0	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



1.0 T<sub>A</sub> = 150°C 125°C 125°C 10.01 0.001 0 5.0 10 15 20 25 V<sub>R</sub>, REVERSE VOLTAGE (VOLTS)

Figure 1. Typical Forward Voltage

Figure 2. Reverse Current versus Reverse Voltage

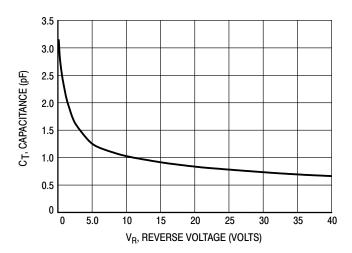


Figure 3. Typical Capacitance

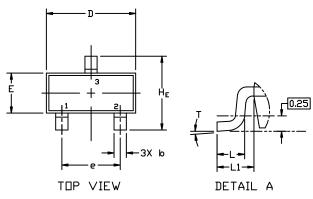


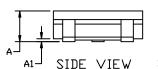


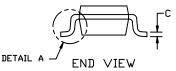
**SOT-23 (TO-236)** CASE 318 ISSUE AT

**DATE 01 MAR 2023** 









#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		INCHES			
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

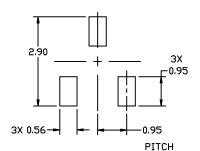
# GENERIC MARKING DIAGRAM\*



XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **STYLES ON PAGE 2**

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE		PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE		2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE		3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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